Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- · Very fast switching
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- High-speed line driver
- · Low-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	210	mA	
Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C		-	2.1	3.5	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	∏6 ∏5 ∏4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 A A G2
4	S2	source TR2	1 2 3	
5	G2	gate TR2	TSSOP6 (SOT363)	N
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX138BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	210	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	135	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	855	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	860	mW
Per device						,
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode			'		,
I _S	source current	T _{amb} = 25 °C	[1]	-	170	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

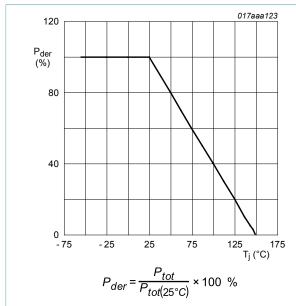


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

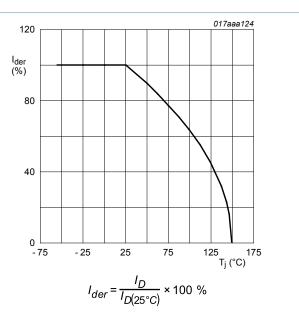


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

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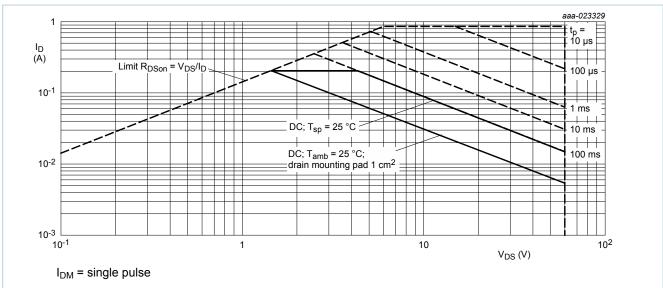


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

8. Thermal characteristics

Table 5. Thermal characteristics

		,					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
fro	thermal resistance from junction to ambient		[1]	-	380	440	K/W
			[2]	-	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	125	145	K/W

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 $\rm cm^2$.

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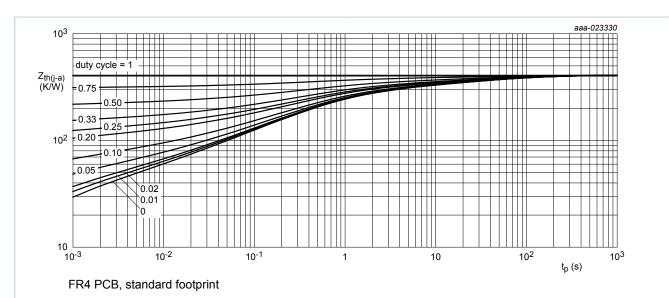


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

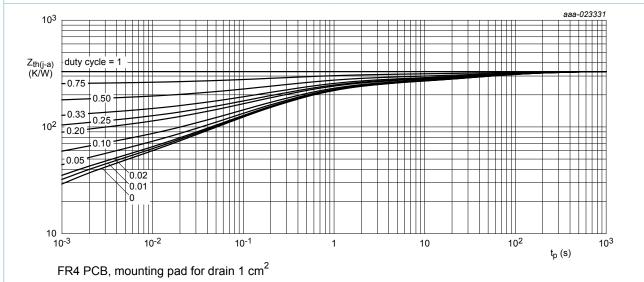


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)		,			
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μΑ
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	2.1	3.5	Ω
	resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 150 °C	-	4.3	7.2	Ω
		V _{GS} = 5 V; I _D = 170 mA; T _j = 25 °C	-	2.2	3.8	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 75 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	2.6	5	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	0.7	-	S
Dynamic cl	naracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	0.5	0.7	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.12	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	20	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.1	-	pF
C _{rss}	reverse transfer capacitance		-	2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	13	-	ns
t _f	fall time		-	5	-	ns
Source-dra	in diode (per transistor)		'	,	,	,
V_{SD}	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	0.9	1.2	V

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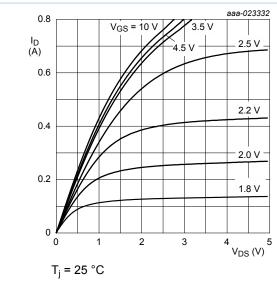


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

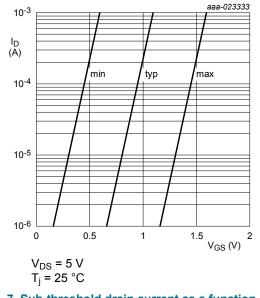


Fig. 7. Sub-threshold drain current as a function of gatesource voltage

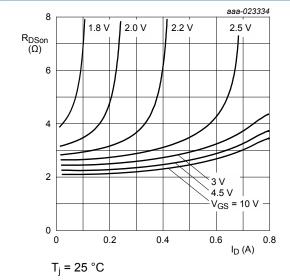


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

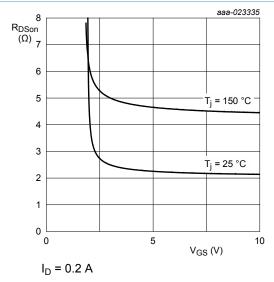


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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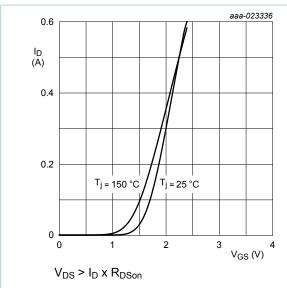


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

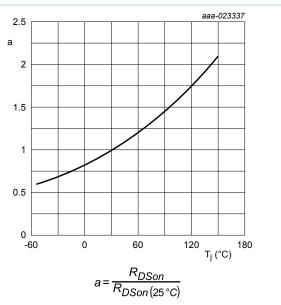


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

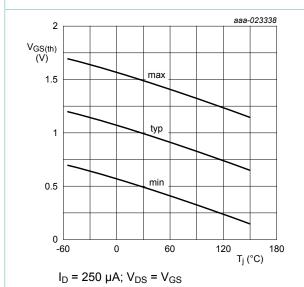


Fig. 12. Gate-source threshold voltage as a function of junction temperature

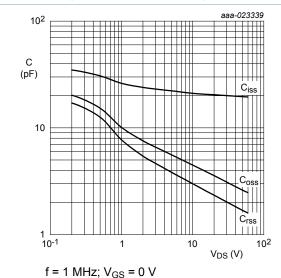


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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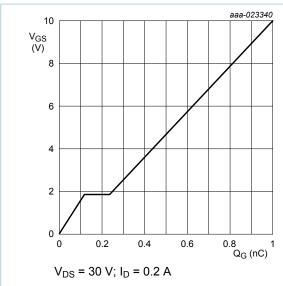


Fig. 14. Gate-source voltage as a function of gate charge; typical values

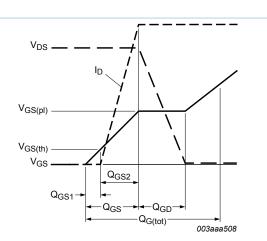


Fig. 15. MOSFET transistor: Gate charge waveform definitions

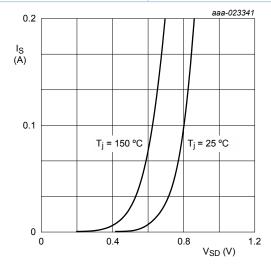
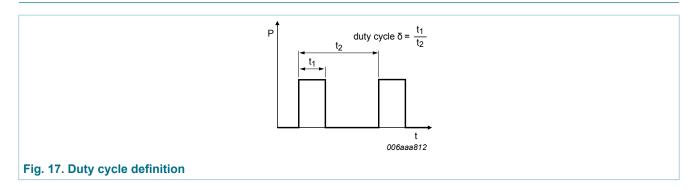


Fig. 16. Source current as a function of source-drain voltage; typical values

10. Test information

 $V_{GS} = 0 V$



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11. Package outline

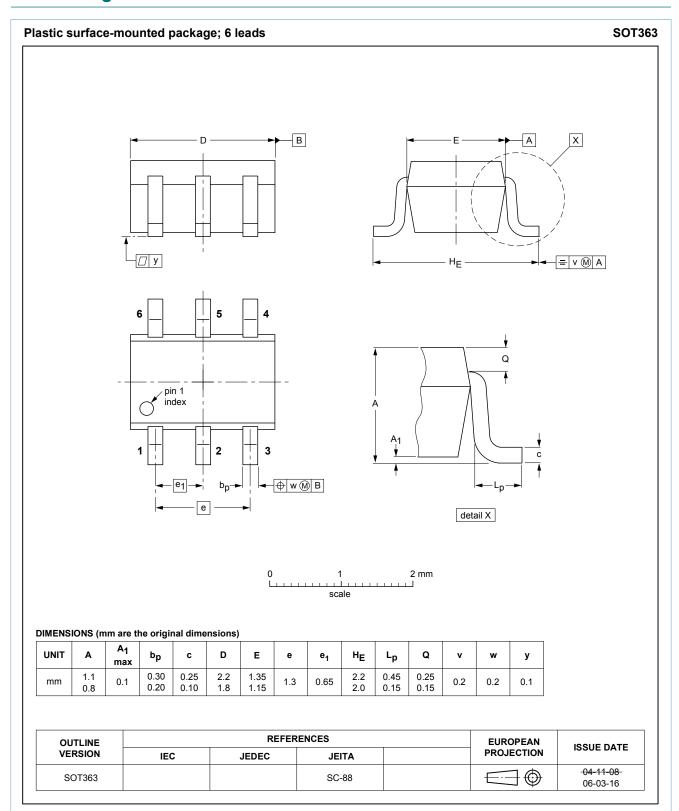
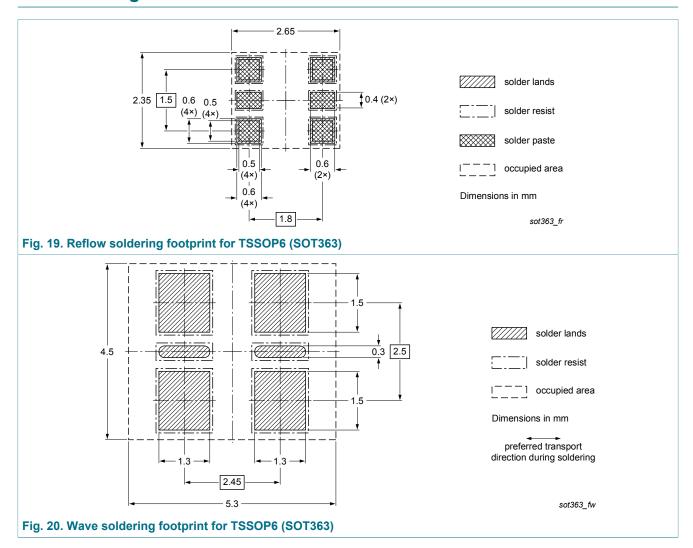


Fig. 18. Package outline TSSOP6 (SOT363)

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12. Soldering



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13. Revision history

Table 7. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BKS v.1	20160615	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NX138BKS

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